

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	5	xie near james.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 08:52
2	BRS	L2	2025	438/692.ccls.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 08:55
3	BRS	L3	137	2 and (cmp near15 acid)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:01

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	0	2 and (cmp near15 acid) near15 (passiv\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:01
5	BRS	L5	0	2 and (cmp near15 acid) near25 (passiv\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:01
6	BRS	L6	0	2 and (cmp near15 acid) near25 (silver or ag)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:02

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	0	2 and (cmp near15 acid) near45 (silver or ag)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/29 09:02
8	BRS	L8	2	(cmp near15 acid) near45 (silver or ag)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/29 09:03
9	BRS	L9	18182	(cmp or chemical) near45 (silver or ag)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/29 09:03

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	122	(cmp or chemical-mechanical) near45 (silver or ag)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:04
11	BRS	L11	191	(cmp or chemical-mechanical) near45 (silver or ag or passiv\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:04
12	BRS	L12	165	(cmp or chemical-mechanical) near45 (silver or ag or passive)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:37

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	1893	(recess or depress\$3) near45 (silver or ag or passive)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:37
14	BRS	L14	0	(recess or depress\$3 or void) near45 (silver or ag or passive) near15 (cmp)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:38
15	BRS	L15	0	(recess or depress\$3 or void) near45 (silver or ag or passive) near15 (chemical-mechanical)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:38

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	0	(recess or depress\$3 or void) near45 (silver or ag or passive) near35 (chemical-mechanical)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:38
17	BRS	L17	33	(recess or depress\$3 or void) near45 (silver or ag or passive) and (chemical-mechanical)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:44
18	BRS	L18	35	(depress\$3 or void) near45 (silver or ag or passive) and (chemical-mechanical or cmp)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:45

	Type	L #	Hits	Search Text	DBs	Time Stamp
19	BRS	L19	28	(depress\$3 or void) near15 (silver or ag or passive) and (chemical-mechanical or cmp)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:48
20	BRS	L20	225	(depress\$3 or void) near15 (silver or ag or cu or passive) and (chemical-mechanical or cmp)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:48
21	BRS	L21	7	(depress\$3 or void) near15 (silver or ag or cu or passive) and ((post) near3 (chemical-mechanical or cmp))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/2 9 09:49

	U	1	Document ID	Title	Current OR
1			US 20030176064 A1	Pre-ECD wet surface modification to improve wettability and reduce void defect	438/687
2			US 20010046786 A1	High-temperature high-pressure processing method for semiconductor wafers, and an anti-oxidizing body used for the method	438/758
3			US 6730597 B1	Pre-ECD wet surface modification to improve wettability and reduced void defect	438/677
4			US 6706625 B1	Copper recess formation using chemical process for fabricating barrier cap for lines and vias	438/637
5			US 6455446 B2	High-temperature high-pressure processing method for semiconductor wafers, and an anti-oxidizing body used for the method	438/795
6			US 6403466 B1	Post-CMP-Cu deposition and CMP to eliminate surface voids	438/627

	U	1	Document ID	Title	Current OR
7			US 6355147 B1	Porous electrode apparatus for electrodeposition of detailed metal structures or microelectronic interconnections	204/242